

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: RHRG75120

MANUFACTURER: INTERSIL

REMARK: TC=80C

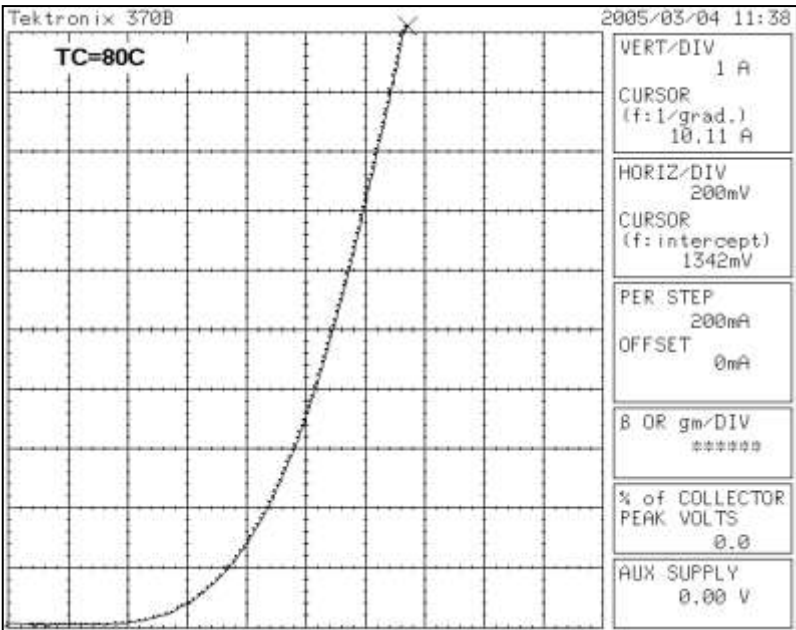


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

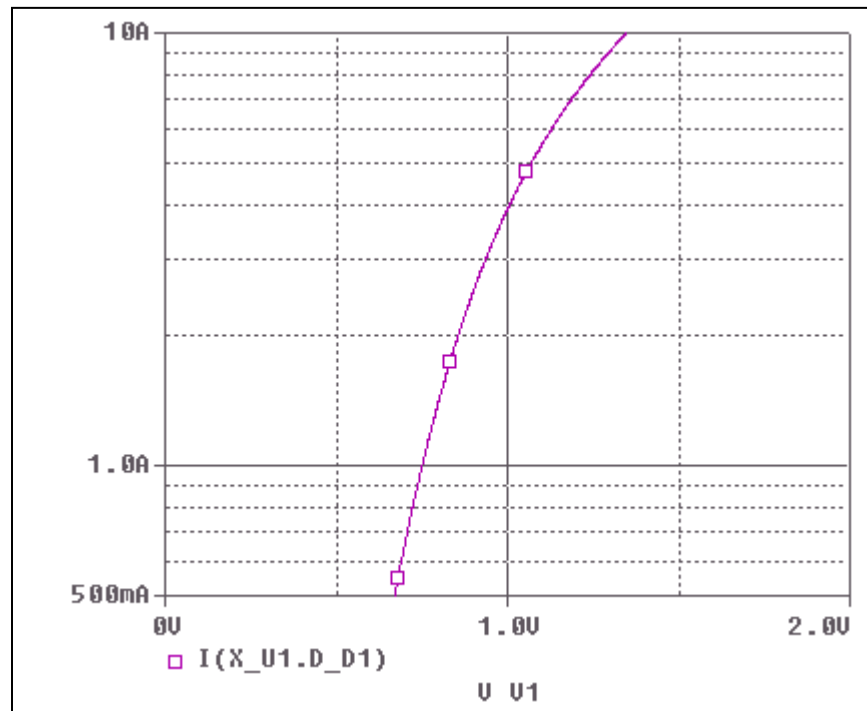
Forward Current Characteristic

Reference

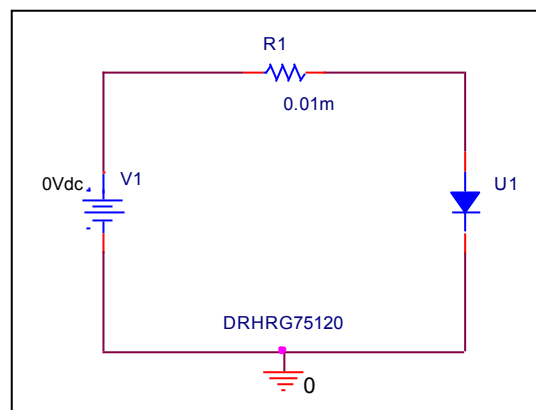


Forward Current Characteristic

Circuit Simulation Result

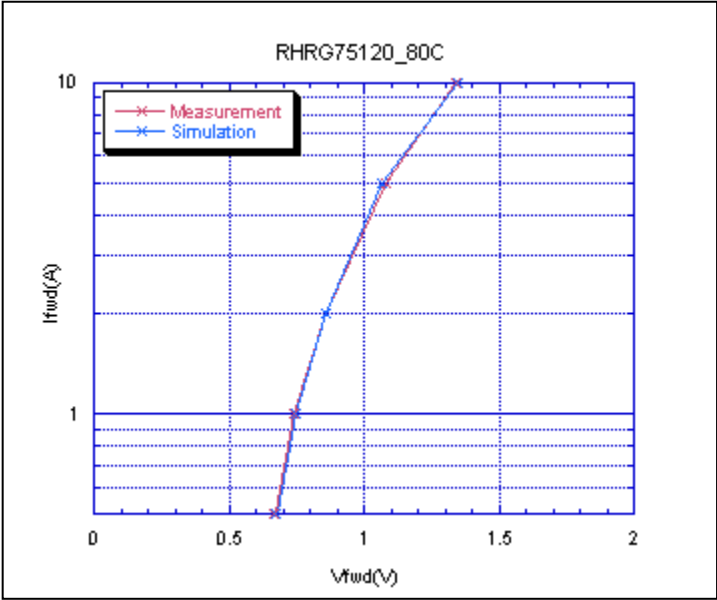


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

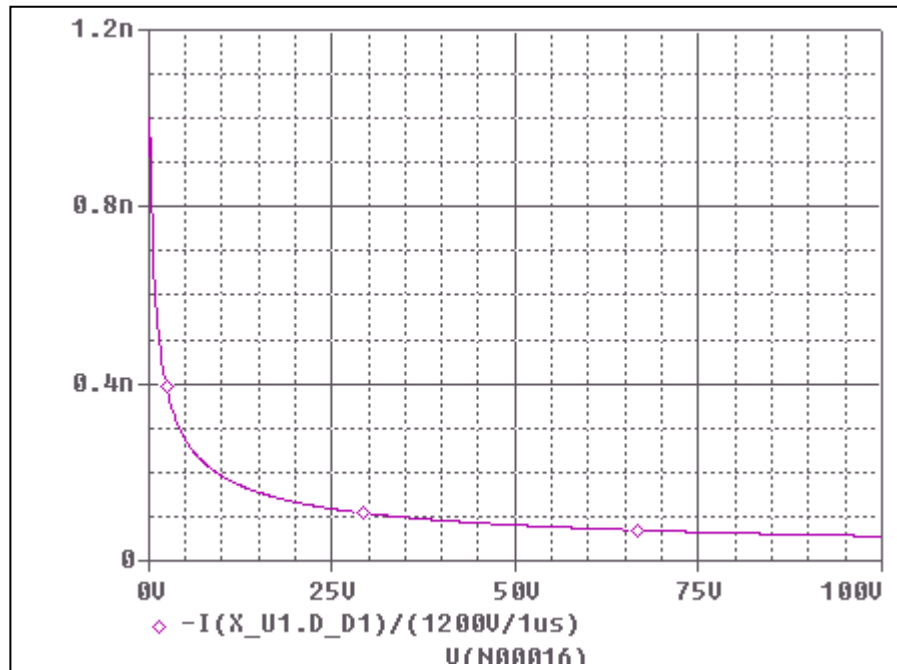


Simulation Result

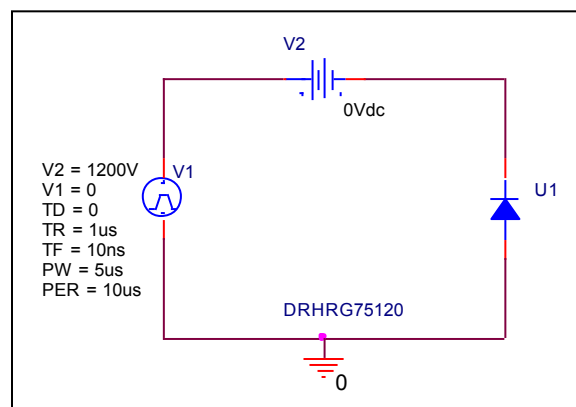
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.5	0.664	0.671	-1.05
1	0.744	0.751	-0.94
2	0.862	0.856	0.70
5	1.080	1.068	1.11
10	1.342	1.349	-0.52

Capacitance Characteristic

Circuit Simulation Result

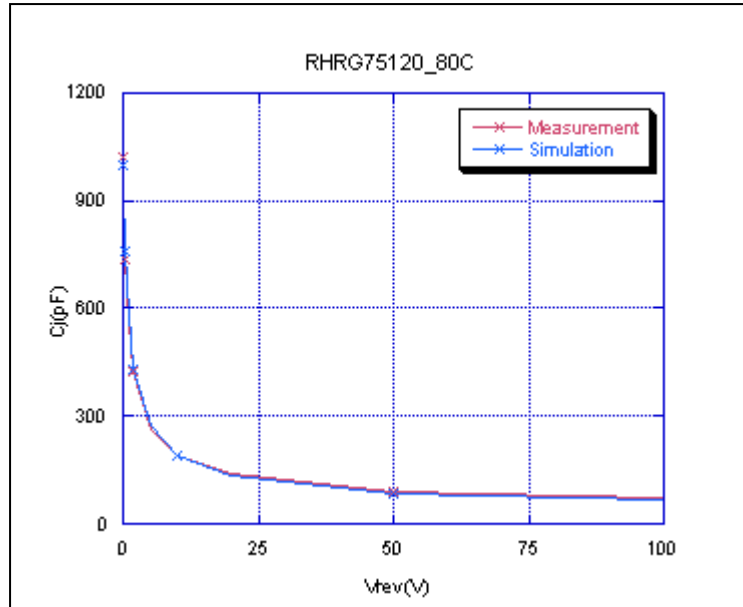


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

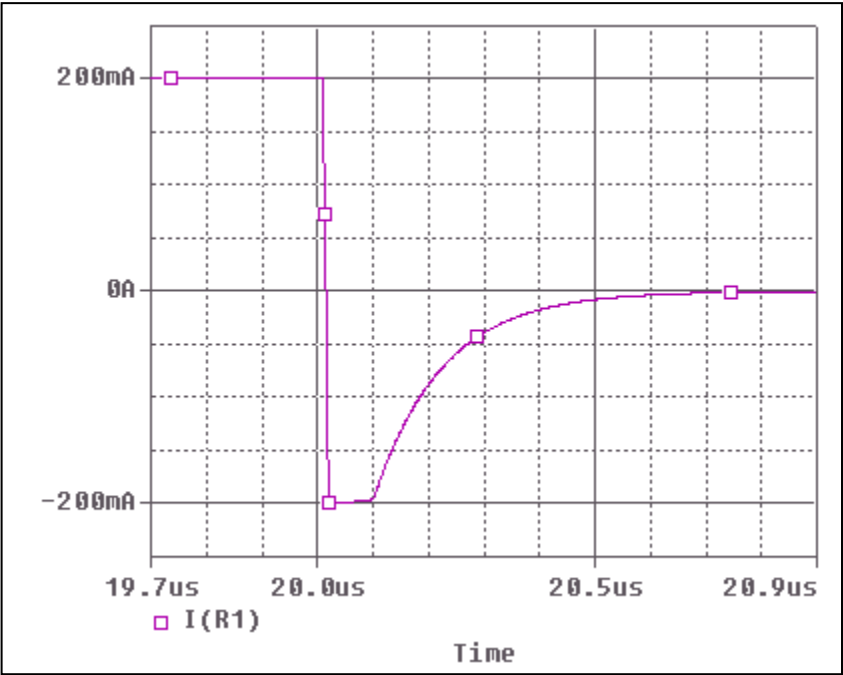


Simulation Result

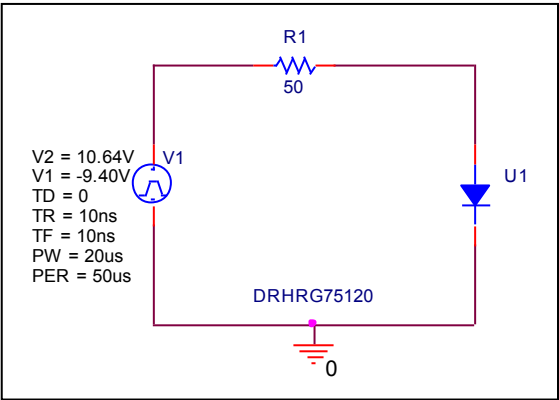
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	1124.000	1124.000	0.00
0.1	1018.000	996.450	2.12
0.2	909.970	934.412	-2.69
0.5	736.170	758.786	-3.07
1	565.450	587.225	-3.85
2	422.040	431.200	-2.17
5	263.380	274.237	-4.12
10	190.800	191.832	-0.54
20	138.540	133.439	3.68

Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

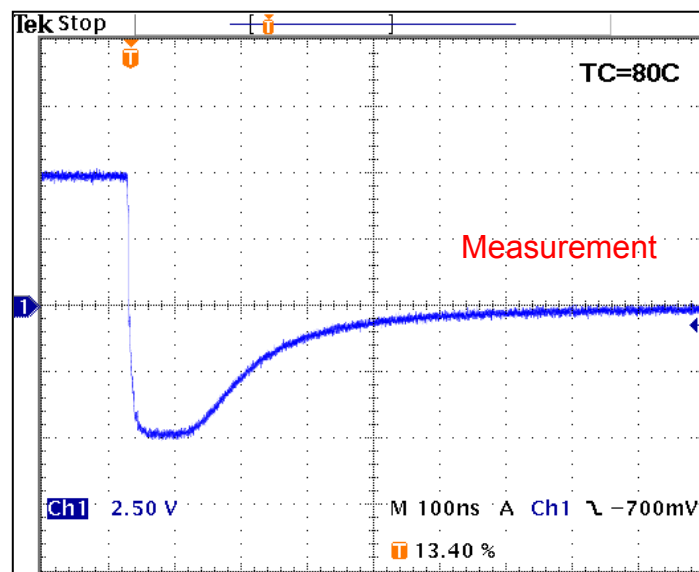


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	86.0	ns	85.3	ns	0.81
trb	282.0	ns	282.1	ns	0.03

Reverse Recovery Characteristic

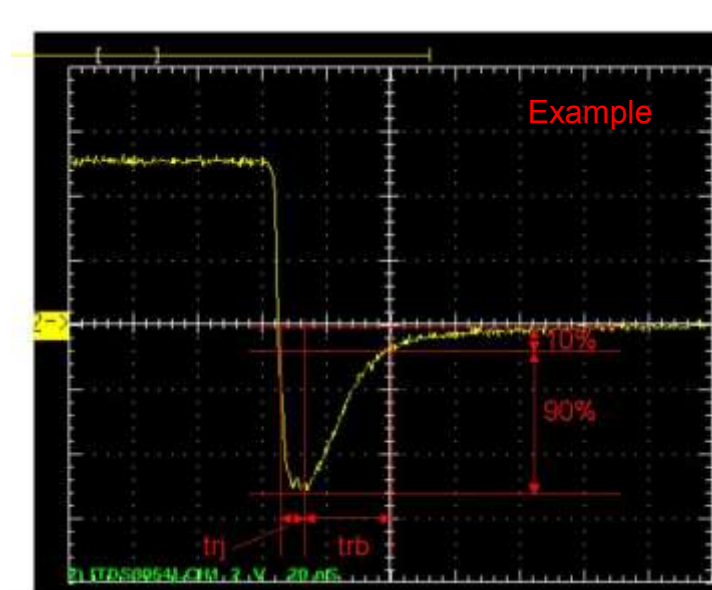
Reference



$T_{rr} = 86$ (ns)

$T_{rb} = 282$ (ns)

Conditions: $I_{fwd} = I_{rev} = 0.2$ (A), $R_I = 50$



Relation between t_{rr} and t_{rb}